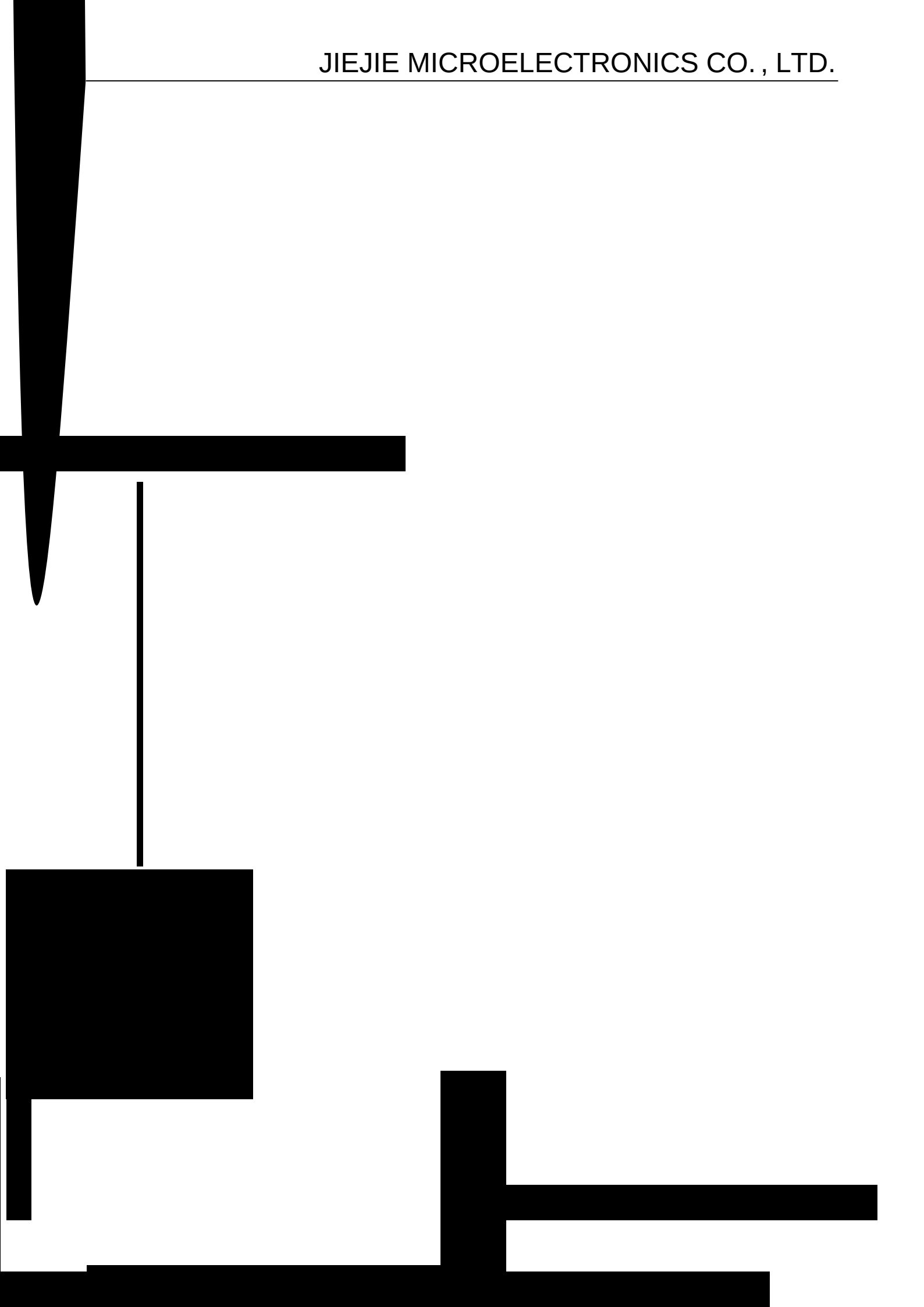




Peak gate current ($t_p=20\text{ }\mu\text{s}$, $T_j=150\text{ }^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150\text{ }^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25\text{ }^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	4.5	kV

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	- -	MAX.	25	mA
V _{GT}		- -	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =150 R _L =3.3k	- -	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	-	MAX.	40	mA
				60	
I _H	I _T =500mA		MAX.	30	mA
dV/dt	V _D =540V Gate Open T _j =125		MIN.	5000	V s
	V _D =540V Gate Open T _j =150			2000	
(dI/dt) _c	(dV/dt) _c =1 9 V _j =150		MIN.	15	A/ms
t _{on}	I _G =40mA I _A =200mA I _R =20mA		TYP.	2	s
t _{off}	T _j =25			30	
V _{CL}	I _{CL} =0.1mA t _p =1ms		MIN.	850	V

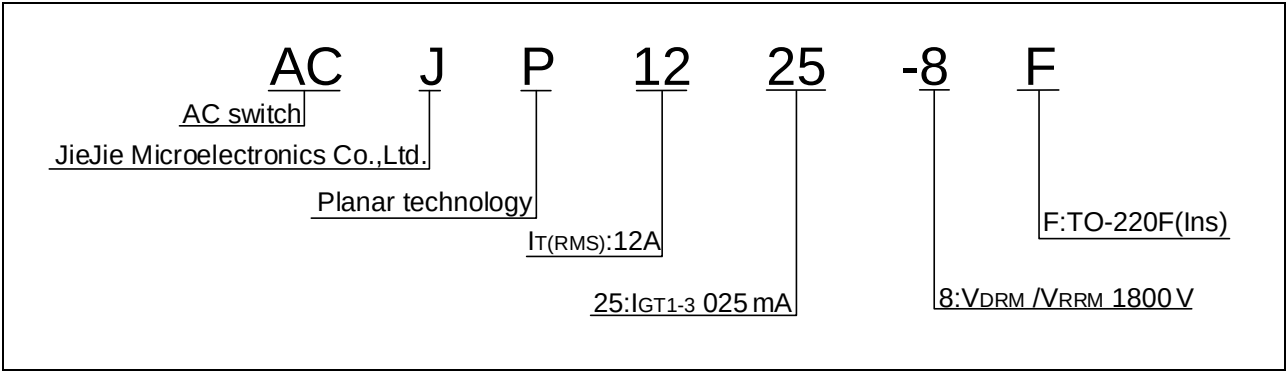
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=17\text{A}$ $t_p=380\text{ }\mu\text{s}$	$T_j=25\text{ }^\circ\text{C}$	1.55	V
V_{TO}	Threshold voltage	$T_j=150\text{ }^\circ\text{C}$	0.73	V
R_D	Dynamic resistance	$T_j=150\text{ }^\circ\text{C}$	40	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25\text{ }^\circ\text{C}$	3	A
I_{RRM}		$T_j=150\text{ }^\circ\text{C}$	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.8	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	50	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

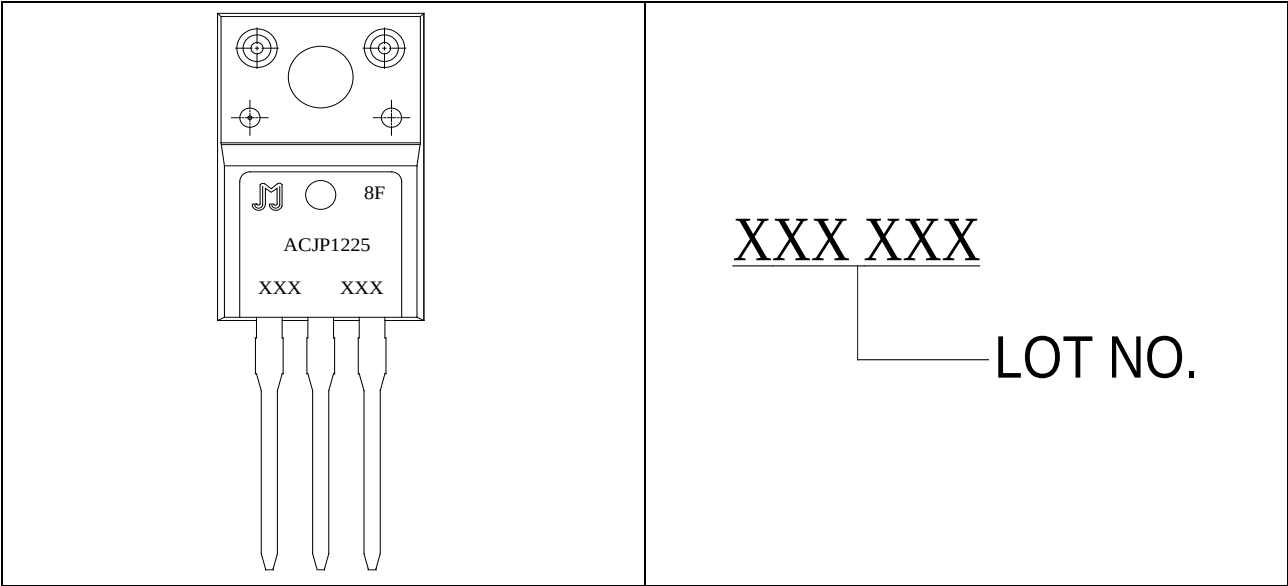


FIG.1: Maximum power dissipation versus RMS on-state current

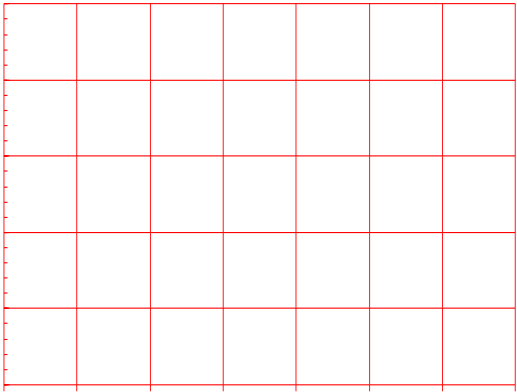


FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards

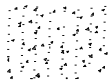
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJP1225-8F	800	25	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2026	A.1.0	Last updated

PACKAGE MECHANICAL DATA



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